

Abstracts

Monolithic InP HEMT V-Band Low-Noise Amplifier

*R.T. Webster, A.J. Slobodnik, Jr. and G.A. Roberts. "Monolithic InP HEMT V-Band Low-Noise Amplifier." 1992 *Microwave and Guided Wave Letters* 2.6 (Jun. 1992 [MGWL]): 236-238.*

A fully monolithic iridium phosphide high electron mobility transistor (InP HEMT) two-stage low-noise amplifier has achieved a noise figure of 4.2 dB with an associated gain of 15.25 dB over the band from 56 to 60 GHz. All noise matching and bias decoupling are accomplished on-chip. The successful performance of the amplifier is credited to accurate characterization of the active and passive devices that make up the circuit.

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